

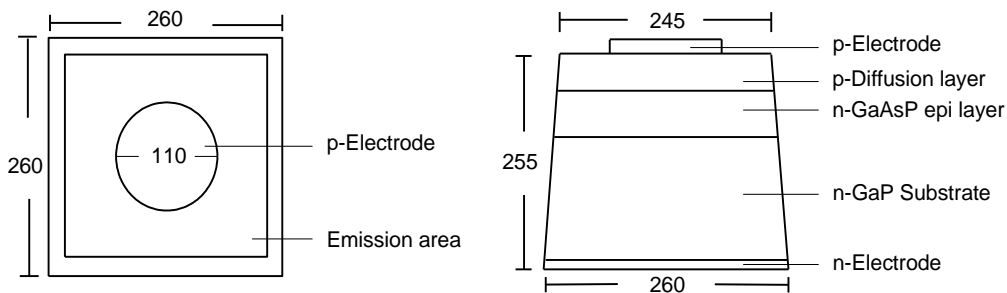
### ■ Features :

- GaAsP/GaP Epi Wafer

### ■ Typical Applications :

- Lamp
- SMD
- Display
- Dot Matrix

### ■ Outline Dimensions : (Unit:um)



### ■ Physical Structure :

Chip dimension	Chip size	260 um x 260 um
	Thickness	255 um
	Emission area	245 um
	Bonding pad	110 um
Electrode	Top: P (anode)	Aluminum (Gold optional)
	Backside: N (cathode)	Gold alloy
Surface condition	Not frosted	

### ■ Electro-Optical Characteristics : (Ta = 25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	$V_F$	$I_F = 20 \text{ mA}$	-	1.95	2.60	V
Reverse Current	$I_R$	$V_R = 5 \text{ V}$	-	-	10	uA
Wavelength	$\lambda_P$	$I_F = 20 \text{ mA}$	-	632	-	nm
	Hue		-	620	-	
Spectral width at half height	$\Delta \lambda$	$I_F = 20 \text{ mA}$	-	35	-	nm
Luminous Intensity	$I_v$	$I_F = 20 \text{ mA}$	7.0	-	-	mcd

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

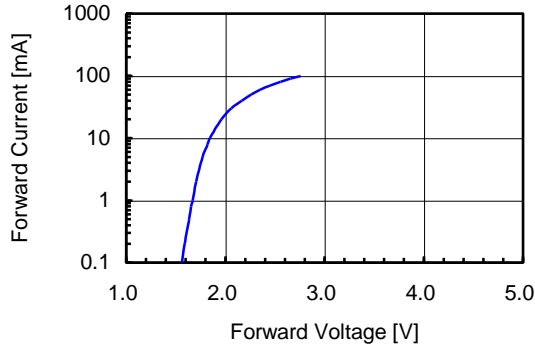


Fig 2. Relative Intensity vs. Forward Current

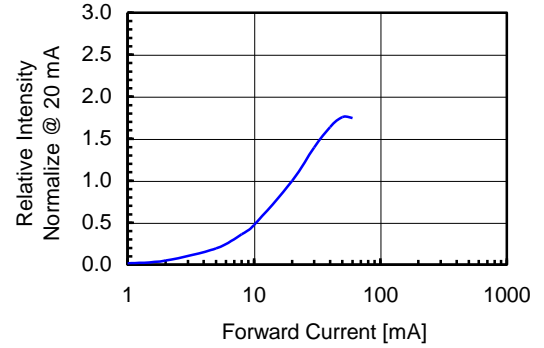


Fig 3. Forward Voltage vs. Temperature

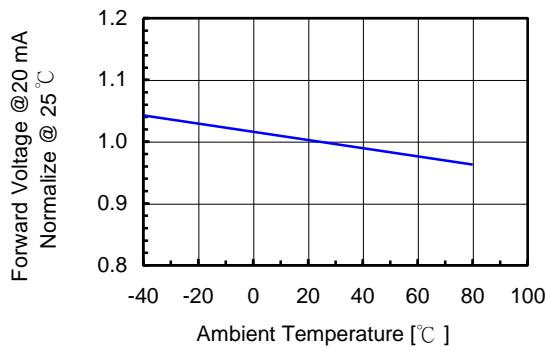


Fig 4. Relative Intensity vs. Temperature

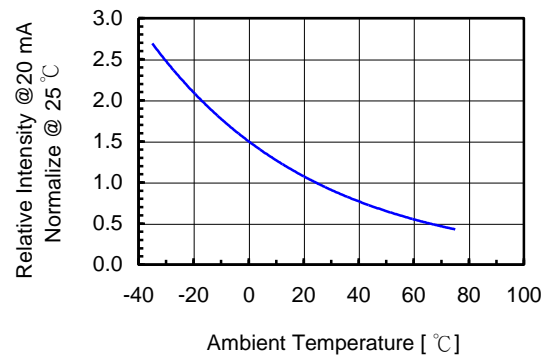


Fig 5. Relative Intensity vs. Wavelength

